Eric TourniÃ©

List of Publications by Year
in descending order

293 papers	5,163 citations	87888 38 h-index	175258 52 g-index
300 all docs	300 docs citations	300 times ranked	3636 citing authors

#	Article	IF	Citations
1	Effects of low temperature on the cold start gaseous emissions from light duty vehicles fuelled by ethanol-blended gasoline. Applied Energy, 2013, 102, 44-54.	10.1	140
2	On the origin of carrier localization in Ga1â^'xInxNyAs1â^'y/GaAs quantum wells. Applied Physics Letters, 2001, 78, 1562-1564.	3.3	130
3	Silicon-Based Photonic Integration Beyond the Telecommunication Wavelength Range. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 394-404.	2.9	106
4	Mechanisms affecting the photoluminescence spectra of GaInNAs after post-growth annealing. Applied Physics Letters, 2002, 80, 4148-4150.	3.3	85
5	Silicon-on-insulator spectrometers with integrated GaInAsSb photodiodes for wide-band spectroscopy from 1510 to 2300 nm. Optics Express, 2013, 21, 6101.	3.4	82
6	Surfactant-mediated molecular beam epitaxy of strained layer semiconductor heterostructures. Thin Solid Films, 1993, 231, 43-60.	1.8	81
7	Near-Field Thermophotovoltaic Conversion with High Electrical Power Density and Cell Efficiency above 14%. Nano Letters, 2021, 21, 4524-4529.	9.1	79
8	Continuous-wave operation above room temperature of GaSb-based laser diodes grown on Si. Applied Physics Letters, 2011, 99, .	3.3	78
9	Nanoindentation of Si, GaP, GaAs and ZnSe single crystals. Journal Physics D: Applied Physics, 2003, 36, L5-L9.	2.8	74
10	GaSb-Based Laser, Monolithically Grown on Silicon Substrate, Emitting at 1.55 mum at Room Temperature. IEEE Photonics Technology Letters, 2010, 22, 553-555.	2.5	67
11	Silicon-based heterogeneous photonic integrated circuits for the mid-infrared. Optical Materials Express, 2013, 3, 1523.	3.0	65
12	Novel plastic strainâ€relaxation mode in highly mismatched IIIâ€V layers induced by twoâ€dimensional epitaxial growth. Applied Physics Letters, 1995, 66, 2265-2267.	3.3	63
13	Annealing effects on the crystal structure of GaInNAs quantum wells with large In and N content grown by molecular beam epitaxy. Journal of Applied Physics, 2003, 94, 2319-2324.	2.5	60
14	Localized surface plasmon resonances in highly doped semiconductors nanostructures. Applied Physics Letters, 2012, 101, .	3.3	58
15	Nanoscale analysis of the In and N spatial redistributions upon annealing of GaInNAs quantum wells. Applied Physics Letters, 2004, 84, 2503-2505.	3.3	57
16	Quantum cascade lasers grown on silicon. Scientific Reports, 2018, 8, 7206.	3.3	56
17	Brewster â€œmodeâ€• in highly doped semiconductor layers: an all-optical technique to monitor doping concentration. Optics Express, 2014, 22, 24294.	3.4	54
18	Study of evanescently-coupled and grating-assisted GaInAsSb photodiodes integrated on a silicon photonic chip. Optics Express, 2012, 20, 11665.	3.4	51

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19	Structural and optical properties of Al0.48In0.52As layers grown on InP by molecular beam epitaxy: Influence of the substrate temperature and of a buffer layer. Journal of Applied Physics, 1991, 70, 7362-7369.	2.5	49
20	Scattered light noise in gravitational wave interferometric detectors: A statistical approach. Physical Review D, 1997, 56, 6085-6095.	4.7	47
21	Nature of the band gap inZn1â^'xBexSealloys. Physical Review B, 2000, 61, 5332-5336.	3.2	47
22	Interface analysis of InAs/GaSb superlattice grown by MBE. Journal of Crystal Growth, 2007, 301-302, 889-892.	1.5	47
23	Metamorphic IIIâ€"V semiconductor lasers grown on silicon. MRS Bulletin, 2016, 41, 218-223.	3.5	47
24	GaSbBi/GaSb quantum well laser diodes. Applied Physics Letters, 2017, 110, .	3.3	45
25	Structural and optical characterization of ZnSe single crystals grown by solidâ€phase recrystallization. Journal of Applied Physics, 1996, 80, 2983-2989.	2.5	44
26	Interfacial intermixing in InAs/GaSb short-period-superlattices grown by molecular beam epitaxy. Applied Physics Letters, 2010, 96, .	3.3	44
27	Photoluminescence of virtualâ€surfactant grown InAs/Al0.48In0.52As single quantum wells. Applied Physics Letters, 1992, 60, 2877-2879.	3.3	43
28	Universal description of III-V/Si epitaxial growth processes. Physical Review Materials, 2018, 2, .	2.4	43
29	Long wavelength GaInNAs/GaAs quantum-well heterostructures grown by solid-source molecular-beam epitaxy. Applied Physics Letters, 2000, 77, 2189-2191.	3.3	42
30	Mid-Infrared Semiconductor Lasers. Semiconductors and Semimetals, 2012, , 183-226.	0.7	42
31	Mid-infrared laser diodes epitaxially grown on on-axis (001) silicon. Optica, 2020, 7, 263.	9.3	42
32	Photoluminescence study of ZnSe single crystals grown by solidâ€phase recrystallization. Applied Physics Letters, 1996, 68, 1356-1358.	3.3	41
33	High temperature liquid phase epitaxy of (100) oriented GaInAsSb near the miscibility gap boundary. Journal of Crystal Growth, 1990, 104, 683-694.	1.5	40
34	Influence of alloy stability on the photoluminescence properties of GaAsN/GaAs quantum wells grown by molecular beam epitaxy. Applied Physics Letters, 2001, 79, 3404-3406.	3.3	40
35	Decomposition in as-grown (Ga,In)(N,As) quantum wells. Applied Physics Letters, 2005, 87, 171901.	3.3	40
36	GaSb-based, 2.2â€‚Î¼m type-I laser fabricated on GaAs substrate operating continuous wave at room temperature. Applied Physics Letters, 2009, 94, 023506.	3.3	40

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37	Surfactant-mediated molecular-beam epitaxy of IIIâ€“V strained-layer heterostructures. Journal of Crystal Growth, 1995, 150, 460-466.	1.5	39
38	Online characterization of regulated and unregulated gaseous and particulate exhaust emissions from two-stroke mopeds: A chemometric approach. Analytica Chimica Acta, 2012, 717, 28-38.	5.4	39
39	Molecular beam epitaxy and characterization of high Bi content GaSbBi alloys. Journal of Crystal Growth, 2017, 477, 144-148.	1.5	39
40	GaInNAs/GaAs quantum wells grown by molecular-beam epitaxy emitting above 1.5 Î¼m. Applied Physics Letters, 2003, 82, 1845-1847.	3.3	38
41	Structural and optical properties of lattice-matched ZnBeSe layers grown by molecular-beam epitaxy onto GaAs substrates. Applied Physics Letters, 1997, 70, 3564-3566.	3.3	37
42	Evaluation of the potential of ZnSe and Zn(Mg)BeSe compounds for ultraviolet photodetection. IEEE Journal of Quantum Electronics, 2001, 37, 1146-1152.	1.9	37
43	Vibrational evidence for a percolative behavior inZn1âˆ'xBexSe. Physical Review B, 2001, 65, .	3.2	37
44	Room-temperature operation of a 2.25â€‚Î¼m electrically pumped laser fabricated on a silicon substrate. Applied Physics Letters, 2009, 94, .	3.3	37
45	2.5 Î¼m GaInAsSb latticeâ€matched to GaSb by liquid phase epitaxy. Journal of Applied Physics, 1990, 68, 5936-5938.	2.5	36
46	Interplay between the growth temperature, microstructure, and optical properties of GaInNAs quantum wells. Applied Physics Letters, 2003, 82, 3451-3453.	3.3	36
47	Room-temperature continuous-wave operation in the telecom wavelength range of GaSb-based lasers monolithically grown on Si. APL Photonics, 2017, 2, .	5.7	36
48	Spectroscopy of donor-acceptor pairs in nitrogen-doped ZnSe. Physical Review B, 1996, 54, 4714-4721.	3.2	34
49	Correlation between interface structure and light emission at 1.3â€“1.55 Î¼m of (Ga,In)(N,As) diluted nitride heterostructures on GaAs substrates. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 2195.	1.6	34
50	From GaAs:N to oversaturated GaAsN: Analysis of the band-gap reduction. Physical Review B, 2004, 69, .	3.2	34
51	Heterogeneous Integration of GaInAsSb p-i-n Photodiodes on a Silicon-on-Insulator Waveguide Circuit. IEEE Photonics Technology Letters, 2011, 23, 1760-1762.	2.5	34
52	Simulations of heteroepitaxial growth. Journal of Crystal Growth, 1997, 178, 258-267.	1.5	33
53	Mid-infrared GaSb-based EP-VCSEL emitting at 2.63â€…[micro sign]m. Electronics Letters, 2009, 45, 265.	1.0	33
54	Highly doped semiconductor plasmonic nanoantenna arrays for polarization selective broadband surface-enhanced infrared absorption spectroscopy of vanillin. Nanophotonics, 2017, 7, 507-516.	6.0	33

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55	Hetero-epitaxial growth of BexZn1â^'xSe on Si(0 0 1) and GaAs(0 0 1) substrates. Journal of Crystal Growth, 1998, 184-185, 11-15.	1.5	32
56	X-ray diffraction study of GaSb grown by molecular beam epitaxy on silicon substrates. Journal of Crystal Growth, 2016, 439, 33-39.	1.5	32
57	Correlations between structural and optical properties of GaInNAs quantum wells grown by MBE. Journal of Crystal Growth, 2003, 251, 383-387.	1.5	31
58	Molecular-beam epitaxy of InSb/GaSb quantum dots. Journal of Applied Physics, 2007, 101, 124309.	2.5	31
59	Micron-sized liquid nitrogen-cooled indium antimonide photovoltaic cell for near-field thermophotovoltaics. Optics Express, 2019, 27, A11.	3.4	31
60	InAs/Ga0.47In0.53As quantum wells: A new IIIâ€V materials system for light emission in the midâ€infrared wavelength range. Applied Physics Letters, 1992, 61, 2808-2810.	3.3	29
61	Visible-blind ultraviolet photodetectors based on ZnMgBeSe Schottky barrier diodes. Applied Physics Letters, 2001, 78, 4190-4192.	3.3	29
62	GaSb-based VCSELs emitting in the mid-infrared wavelength range (2â€"3Î¼m) grown by MBE. Journal of Crystal Growth, 2009, 311, 1912-1916.	1.5	29
63	Midwave infrared barrier detector based on Ga-free InAs/InAsSb type-II superlattice grown by molecular beam epitaxy on Si substrate. Infrared Physics and Technology, 2019, 96, 39-43.	2.9	29
64	Virtualâ€surfactant epitaxy of strained InAs/Al0.48In0.52As quantum wells. Applied Physics Letters, 1993, 62, 858-860.	3.3	28
65	Interplay between Surface Stabilization, Growth Mode and Strain Relaxation during Molecular-Beam Epitaxy of Highly Mismatched III-V Semiconductor Layers. Europhysics Letters, 1994, 25, 663-668.	2.0	28
66	Surface stoichiometry, epitaxial morphology and strain relaxation during molecular beam epitaxy of highly strained InAs/Ga0.47In0.53As heterostructures. Journal of Crystal Growth, 1994, 135, 97-112.	1.5	28
67	Long-wave phonons inZnSeâ^'BeSemixed crystals: Raman scattering and percolation model. Physical Review B, 2004, 70, .	3.2	28
68	GaInAsSb/GaSb pn photodiodes for detection to 2.4 Î¼m. Electronics Letters, 1991, 27, 1237.	1.0	27
69	Silicon surface preparation for III-V molecular beam epitaxy. Journal of Crystal Growth, 2015, 413, 17-24.	1.5	27
70	Growth limitations by the miscibility gap in liquid phase epitaxy of Ga1â^'xInxAsySb1â^'y on GaSb. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1991, 9, 125-128.	3.5	26
71	High-density, uniform InSbâ^•GaSb quantum dots emitting in the midinfrared region. Applied Physics Letters, 2006, 89, 263118.	3.3	26
72	Silicon-on-insulator shortwave infrared wavelength meter with integrated photodiodes for on-chip laser monitoring. Optics Express, 2014, 22, 27300.	3.4	26

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73	Raman study of ZnxBe1â^’xSe alloy (100) epitaxial layers. Applied Physics Letters, 2000, 77, 519-521.	3.3	25
74	Liquid phase epitaxy and characterization of InAs1- x - ySb x P y on (100) InAs. Journal of Crystal Growth, 1992, 121, 463-472.	1.5	24
75	Growth mechanism of GaAs on (110) GaAs studied by high-energy electron diffraction and atomic force microscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1994, 12, 2574.	1.6	24
76	Defect control during growth of highly mismatched (100). Journal of Crystal Growth, 1995, 146, 368-373.	1.5	24
77	Temperature dependence of the photoluminescence of Zn1â^’xCdxSe/ZnSe strainedâ€layer quantum wells. Applied Physics Letters, 1995, 67, 103-105.	3.3	24
78	Nanoindentation study of Zn1ÂxBexSe heteroepitaxial layers. Journal Physics D: Applied Physics, 2002, 35, 3015-3020.	2.8	24
79	Temperature-dependent terahertz spectroscopy of inverted-band three-layer InAs/GaSb/InAs quantum well. Physical Review B, 2018, 97, .	3.2	24
80	New III-V double-heterojunction laser emitting near 3.2Î¼m. Electronics Letters, 1988, 24, 1542.	1.0	23
81	Zn(Mg)BeSe-based p-i-n photodiodes operating in the blue-violet and near-ultraviolet spectral range. Applied Physics Letters, 2000, 76, 242-244.	3.3	23
82	Interface properties of (Ga,In)(N,As) and (Ga,In)(As,Sb) materials systems grown by molecular beam epitaxy. Journal of Crystal Growth, 2009, 311, 1739-1744.	1.5	23
83	Localized surface plasmon resonance frequency tuning in highly doped InAsSb/GaSb one-dimensional nanostructures. Nanotechnology, 2016, 27, 425201.	2.6	23
84	Zinc-blende group III-V/group IV epitaxy: Importance of the miscut. Physical Review Materials, 2020, 4, .	2.4	23
85	Self-compensation in nitrogen-doped ZnSe. Physical Review B, 1997, 56, R1657-R1660.	3.2	22
86	Spectroscopy of the phosphorus impurity in ZnSe epitaxial layers grown by molecular-beam epitaxy. Physical Review B, 2000, 61, 15789-15796.	3.2	22
87	Single-Mode Monolithic GaSb Vertical-Cavity Surface-Emitting Laser. Optics Express, 2012, 20, 15540.	3.4	22
88	A Stressâ€Free and Textured GaP Template on Silicon for Solar Water Splitting. Advanced Functional Materials, 2018, 28, 1801585.	14.9	22
89	InAs-based quantum cascade lasers grown on on-axis (001) silicon substrate. APL Photonics, 2020, 5, .	5.7	22
90	Subpicosecond timescale carrier dynamics in GaInAsSbâ^•AlGaAsSb double quantum wells emitting at 2.3Î¼m. Applied Physics Letters, 2008, 92, .	3.3	20

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91	Mid-infrared IIIâ€"V semiconductor lasers epitaxially grown on Si substrates. Light: Science and Applications, 2022, 11, .	16.6	20
92	Strained InAs single quantum wells embedded in a Ga0.47In0.53As matrix. Applied Physics Letters, 1992, 61, 846-848.	3.3	19
93	ZnSe-based Schottky barrier photodetectors. Electronics Letters, 2000, 36, 352.	1.0	19
94	Analysis of epitaxial GaxIn1â^'xAs/InP and AlyIn1â^'yAs/InP interface region by high resolution xâ€ray diffraction. Applied Physics Letters, 1993, 62, 149-151.	3.3	18
95	Defect density in ZnSe pseudomorphic layers grown by molecular beam epitaxy on to various GaAs buffer layers. Journal of Crystal Growth, 1998, 192, 102-108.	1.5	18
96	Percolation-based vibrational picture to estimate nonrandom N substitution in GaAsN alloys. Applied Physics Letters, 2003, 82, 2808-2810.	3.3	18
97	High-density InSb-based quantum dots emitting in the mid-infrared. Journal of Crystal Growth, 2007, 301-302, 713-717.	1.5	18
98	Anti phase boundary free GaSb layer grown on 300 mm (001)-Si substrate by metal organic chemical vapor deposition. Thin Solid Films, 2018, 645, 5-9.	1.8	18
99	Crystal Phase Control during Epitaxial Hybridization of IIIâ€V Semiconductors with Silicon. Advanced Electronic Materials, 2022, 8, 2100777.	5.1	18
100	Virtual-surfactant epitaxy of InAs quantum wells. Journal of Crystal Growth, 1993, 127, 765-769.	1.5	17
101	Anisotropic misfit dislocation nucleation in two-dimensional grown InAs/GaAs(001) heterostructures. Applied Physics Letters, 1998, 73, 1074-1076.	3.3	17
102	Evidence of N-related compensating donors in lightly doped ZnSe:N. Applied Physics Letters, 1999, 74, 2200-2202.	3.3	17
103	Recombination channels in 2.4â€"3.2 Âµm GaInAsSb quantum-well lasers. Semiconductor Science and Technology, 2013, 28, 015015.	2.0	17
104	Effect of nitrogen on the band structure and material gain of In/sub y/Ga/sub 1-y/As/sub 1-x/N/sub x/-GaAs quantum wells. IEEE Journal of Selected Topics in Quantum Electronics, 2003, 9, 716-722.	2.9	16
105	Type I GaSb1-xBix/GaSb quantum wells dedicated for mid infrared laser applications: Photoreflectance studies of bandgap alignment. Journal of Applied Physics, 2019, 125, .	2.5	16
106	Virtual-surfactant-induced wetting in strained-layer heteroepitaxy. Applied Physics A: Solids and Surfaces, 1993, 56, 91-94.	1.4	15
107	Heteroepitaxial growth of BeSe on vicinal Si(001) surfaces. Applied Physics Letters, 1998, 73, 957-959.	3.3	15
108	InAs/GaSb short-period superlattice injection lasers operating in 2.5â€…[micro sign]mâ€"3.5â€…[micro sign]m mid-infrared wavelength range. Electronics Letters, 2007, 43, 1285.	1.0	15

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109	Mid-infrared characterization of refractive indices and propagation losses in GaSb/AlXGa1â˜’XAsSb waveguides. Applied Physics Letters, 2015, 107, .	3.3	15
110	Characterization of antimonide based material grown by molecular epitaxy on vicinal silicon substrates via a low temperature AlSb nucleation layer. Journal of Crystal Growth, 2017, 477, 65-71.	1.5	15
111	Surface-enhanced infrared absorption with Si-doped InAsSb/GaSb nano-antennas. Optics Express, 2017, 25, 26651.	3.4	15
112	Indium antimonide photovoltaic cells for near-field thermophotovoltaics. Solar Energy Materials and Solar Cells, 2019, 203, 110190.	6.2	15
113	(001) GaAs substrate preparation for direct ZnSe heteroepitaxy. Journal of Applied Physics, 1997, 81, 7012-7017.	2.5	14
114	p-type doping of Zn(Mg)BeSe epitaxial layers. Applied Physics Letters, 1999, 75, 382-384.	3.3	14
115	Raman study of Zn1â˜’xBexSe/GaAs systems with low Be content (xâ©½0.20). Journal of Applied Physics, 2002, 91, 9187-9197.	2.5	14
116	Isoelectronic traps in heavily doped GaAs:(In,N). Physical Review B, 2003, 68, .	3.2	14
117	Optical performances of InAs/GaSb/InSb short-period superlattice laser diode for mid-infrared emission. Journal of Applied Physics, 2010, 108, 093107.	2.5	14
118	Modelling of an InAs/GaSb/InSb short-period superlattice laser diode for mid-infrared emission by the k.p method. Journal Physics D: Applied Physics, 2010, 43, 325102.	2.8	14
119	Mid-IR GaSb-Based Bipolar Cascade VCSELs. IEEE Photonics Technology Letters, 2013, 25, 882-884.	2.5	14
120	Low-loss orientation-patterned GaSb waveguides for mid-infrared parametric conversion. Optical Materials Express, 2017, 7, 3011.	3.0	14
121	Microstructure and interface analysis of emerging Ga(Sb,Bi) epilayers and Ga(Sb,Bi)/GaSb quantum wells for optoelectronic applications. Applied Physics Letters, 2018, 112, .	3.3	14
122	Interface energy analysis of IIIâ€“V islands on Si (001) in the Volmer-Weber growth mode. Applied Physics Letters, 2018, 113, .	3.3	14
123	Improved efficiency of GaSb solar cells using an Al0.50Ga0.50As0.04Sb0.96 window layer. Solar Energy Materials and Solar Cells, 2019, 200, 110042.	6.2	14
124	Massless Dirac fermions in III-V semiconductor quantum wells. Physical Review B, 2019, 99, .	3.2	14
125	Quantum well interband semiconductor lasers highly tolerant to dislocations. Optica, 2021, 8, 1397.	9.3	14
126	Overlayer strain: A key to directly tune the topography of highâ€index semiconductor surfaces. Applied Physics Letters, 1993, 63, 3300-3302.	3.3	13

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127	Long-wavelength strained-layer InAs/GaInAs single-quantum-well laser grown by molecular beam epitaxy on InP substrate. Electronics Letters, 1993, 29, 1255.	1.0	13
128	New results on the solid-phase recrystallisation of ZnSe. Journal of Crystal Growth, 1998, 184-185, 1021-1025.	1.5	13
129	Selective growth of ordered hexagonal InN nanorods. CrystEngComm, 2019, 21, 2702-2708.	2.6	13
130	GaSb-based solar cells for multi-junction integration on Si substrates. Solar Energy Materials and Solar Cells, 2019, 191, 444-450.	6.2	13
131	Structural characterization of lattice matched AlxIn1â^'xAs/InP and GayIn1â^'yAs/InP heterostructures by transmission electron microscopy and highâ€resolution xâ€ray diffraction. Journal of Applied Physics, 1995, 78, 2403-2410.	2.5	12
132	Molecularâ€beam epitaxy of highâ€quality ZnSe homoâ€epitaxial layers on solidâ€phase recrystallized substrates. Applied Physics Letters, 1996, 69, 3221-3223.	3.3	12
133	The phosphorus acceptor in ZnSe. Journal of Crystal Growth, 1998, 184-185, 515-519.	1.5	12
134	Highly tensile-strained, type-II, Ga1â^'xInxAs/GaSb quantum wells. Applied Physics Letters, 2010, 96, .	3.3	12
135	GaSb-based composite quantum wells for laser diodes operating in the telecom wavelength range near 1.55-<i>Î¼</i>m. Applied Physics Letters, 2015, 106, .	3.3	12
136	On the origin of threading dislocations during epitaxial growth of III-Sb on Si(001): A comprehensive transmission electron tomography and microscopy study. Acta Materialia, 2018, 143, 121-129.	7.9	12
137	Phosphonate monolayers on InAsSb and GaSb surfaces for mid-IR plasmonics. Applied Surface Science, 2018, 451, 241-249.	6.1	12
138	Characteristic temperature Toof Ga0.83In0.17As0.15Sb0.85/Al0.27Ga0.73As0.02Sb0.98 injection lasers. Electronics Letters, 1988, 24, 1076.	1.0	12
139	Issues in molecular-beam epitaxy of ZnSe-based heterostructures for blue-green lasers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 43, 21-28.	3.5	11
140	New results and trends in the solid phase recrystallization of ZnSe. Materials Letters, 1998, 36, 162-166.	2.6	11
141	Molecular-beam epitaxy of BeTe layers on GaAs substrates studied via reflection high-energy electron diffraction. Applied Physics Letters, 1998, 72, 2859-2861.	3.3	11
142	Ohmic contacts to p-type ZnSe using a ZnSe/BeTe superlattice. Applied Physics Letters, 1999, 75, 3345-3347.	3.3	11
143	New developments in the heteroepitaxial growth of Be-chalcogenides based semiconducting alloys. Journal of Electronic Materials, 1999, 28, 662-665.	2.2	11
144	Molecular beam epitaxial growth and characterization of Be(Zn)Se on Si(001) and GaAs(001). Journal of Crystal Growth, 2000, 214-215, 95-99.	1.5	11

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145	Electronic structure and radiative lifetimes of ideal Zn1â^'xBexSe alloys. Solid State Communications, 2002, 123, 209-212.	1.9	11
146	Photoluminescence spectroscopy of Ga(In)NAs quantum wells for emission at 1.5 Î¼m. Solid-State Electronics, 2003, 47, 477-482.	1.4	11
147	Does In-bonding delay GaN-segregation in GaInAsN? A Raman study. Applied Physics Letters, 2004, 85, 5872-5874.	3.3	11
148	MBE growth and interface formation of compound semiconductor heterostructures for optoelectronics. Physica Status Solidi (B): Basic Research, 2007, 244, 2683-2696.	1.5	11
149	InAs/GaSb/InSb short-period super-lattice diode lasers emitting near 3.3â€…[micro sign]m at room-temperature. Electronics Letters, 2009, 45, 165.	1.0	11
150	Growth by liquid phase epitaxy and characterization of GaInAsSb and InAsSbP alloys for mid-infrared applications (2-3 um). , 1991, , .		10
151	Fano-like resonances sustained by Si doped InAsSb plasmonic resonators integrated in GaSb matrix. Optics Express, 2015, 23, 29423.	3.4	10
152	Interband cascade Lasers with AlGaAsSb cladding layers emitting at 33â€…Âµm. Optics Express, 2019, 27, 31425.	3.4	10
153	Structural properties and transport characteristics of pseudomorphic GaxIn1â^'xAs/AlyIn1â^'yAs modulationâ€doped heterostructures grown by molecularâ€beam epitaxy. Journal of Applied Physics, 1992, 71, 1790-1797.	2.5	9
154	Optical properties of InAs quantum wells emitting between 0.9 mu m and 2.5 mu m. Semiconductor Science and Technology, 1993, 8, S236-S239.	2.0	9
155	Current Activity in CNRSâ€Sophia Antipolis Regarding Wideâ€Gap IIâ€"VI Materials. Physica Status Solidi (B): Basic Research, 1995, 187, 457-466.	1.5	9
156	Direct evidence for the trigonal symmetry of shallow phosphorus acceptors in ZnSe. Physical Review B, 2001, 64, .	3.2	9
157	Conduction band crossover induced by misfit strain in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi mathvariant="normal">In</mml:mi><mml:mi mathvariant="normal">Sb</mml:mi><mml:mo>â^•</mml:mo><mml:mi mathvariant="normal">Ga</mml:mi><mml:mi mathvariant="normal">Sb</mml:mi></mml:mrow></mml:math>self-assembled quantum dots. Physical R	3.2	9
158	Type II transition in InSb-based nanostructures for midinfrared applications. Journal of Applied Physics, 2008, 103, 114516.	2.5	9
159	Non-random Be-to-Zn substitution in ZnBeSe alloys: Raman scattering and ab initio calculations. European Physical Journal B, 2010, 73, 461-469.	1.5	9
160	Electron tomography on III-Sb heterostructures on vicinal Si(001) substrates: Anti-phase boundaries as a sink for threading dislocations. Scripta Materialia, 2017, 132, 5-8.	5.2	9
161	Growth and characterization of AlInAsSb layers lattice-matched to GaSb. Journal of Crystal Growth, 2017, 477, 72-76.	1.5	9
162	Investigation of AlInAsSb/GaSb tandem cells â€" A first step towards GaSb-based multi-junction solar cells. Solar Energy Materials and Solar Cells, 2021, 219, 110795.	6.2	9

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163	GaSb-based laser diodes grown on MOCVD GaAs-on-Si templates. Optics Express, 2021, 29, 11268.	3.4	9
164	Etched-cavity GaSb laser diodes on a MOVPE GaSb-on-Si template. Optics Express, 2020, 28, 20785.	3.4	9
165	Tunable generation of nanometer-scale corrugations on high-index III-V semiconductor surfaces. Physical Review B, 1994, 49, 11053-11059.	3.2	8
166	Native vacancies in nitrogen-doped and undoped ZnSe layers studied by positron annihilation. Physical Review B, 2000, 62, 15711-15717.	3.2	8
167	Wide-band-gap ZnMgBeSe alloys grown onto GaAs by molecular beam epitaxy. Journal of Crystal Growth, 2001, 223, 461-465.	1.5	8
168	Structural and optical properties of InSb quantum dots for mid-IR applications. Physica Status Solidi (B): Basic Research, 2006, 243, 3959-3962.	1.5	8
169	Note: A high transmission Faraday optical isolator in the 9.2 Î¼m range. Review of Scientific Instruments, 2011, 82, 096106.	1.3	8
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